MOSFETs Silicon N-channel MOS (U-MOSIX-H)

# TPH1R005PL

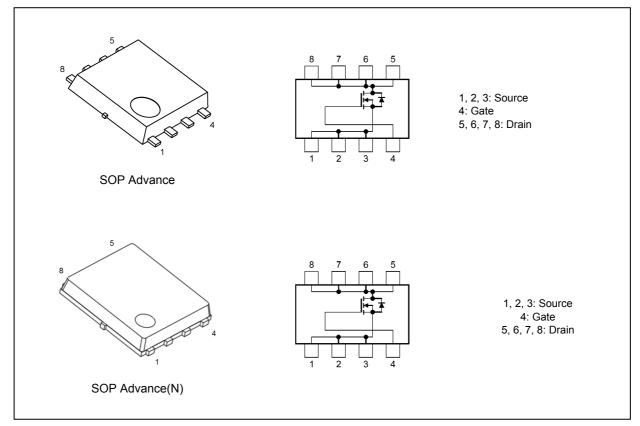
### 1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators

### 2. Features

- (1) High-speed switching
- (2) Small gate charge:  $Q_{SW} = 34 \text{ nC}$  (typ.)
- (3) Small output charge:  $Q_{oss} = 98 \text{ nC}$  (typ.)
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 0.8 \text{ m}\Omega$  (typ.) (V<sub>GS</sub> = 10 V)
- (5) Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 45 \ V)$
- (6) Enhancement mode:  $V_{th}$  = 1.4 to 2.4 V ( $V_{DS}$  = 10 V,  $I_D$  = 1.0 mA)

### 3. Packaging and Internal Circuit



The package can be selected according to your preference. For details, please contact your TOSHIBA sales representative.

### 4. Absolute Maximum Ratings (Note) (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteris	tics		Symbol	Rating	Unit
Drain-source voltage			V <sub>DSS</sub>	45	V
Gate-source voltage			V <sub>GSS</sub>	±20	
Drain current (DC)	(T <sub>c</sub> = 25 °C)	(Note 1), (Note 2)	Ι <sub>D</sub>	150	A
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	Ι <sub>D</sub>	280	A
Drain current (pulsed)	(t = 100 μs)	(Note 1)	I <sub>DP</sub>	500	A
Power dissipation	(T <sub>c</sub> = 25 °C)		PD	170	W
Power dissipation	·	(Note 3)	PD	3.0	W
Power dissipation		(Note 4)	PD	0.96	W
Single-pulse avalanche energy		(Note 5)	E <sub>AS</sub>	243	mJ
Single-pulse avalanche current	·	(Note 5)	I <sub>AS</sub>	120	A
Channel temperature			T <sub>ch</sub>	175	°C
Storage temperature			T <sub>stg</sub>	-55 to 175	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-case thermal resistance	(T <sub>c</sub> = 25 °C)		R <sub>th(ch-c)</sub>	0.88	°C/W
Channel-to-ambient thermal resistance	(T <sub>a</sub> = 25 °C)	(Note 3)	R <sub>th(ch-a)</sub>	50	
Channel-to-ambient thermal resistance	(T <sub>a</sub> = 25 °C)	(Note 4)	R <sub>th(ch-a)</sub>	156	

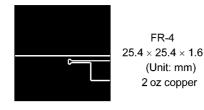
Note 1: Ensure that the channel temperature does not exceed 175 °C.

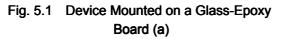
Note 2: Limited by package limit. Silicon chip capability is 280 A. ( $T_c = 25 °C$ )

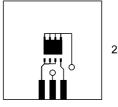
Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V\_DD = 36 V, T\_ch = 25 °C (initial), L = 13  $\mu$ H, I<sub>AS</sub> = 120 A







FR-4 25.4 × 25.4 × 1.6 (Unit: mm) 2 oz copper

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

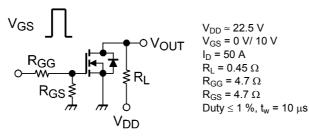
#### 6. Electrical Characteristics

### 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±20 V, $V_{DS}$ = 0 V			±0.1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 45 V, V <sub>GS</sub> = 0 V			10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	45	_	—	V
	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	30	_	_	
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.0 mA	1.4	_	2.4	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 50 A		1.2	1.7	mΩ
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 50 A		0.8	1.04	

### 6.2. Dynamic Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 22.5 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	7700	9600	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	76	_	
Output capacitance	C <sub>oss</sub>			1860	_	
Gate resistance	r <sub>g</sub>	—	_	0.6	1.1	Ω
Switching time (rise time)	tr	See Fig. 6.2.1	_	17	_	ns
Switching time (turn-on time)	t <sub>on</sub>			29	_	
Switching time (fall time)	t <sub>f</sub>	]		18	_	
Switching time (turn-off time)	t <sub>off</sub>	]		75	_	



#### Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics ( $T_a = 25$ °C unless otherwise specified)

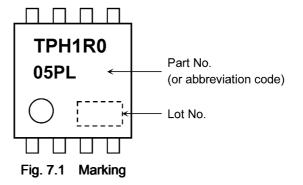
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	Qg	$V_{DD}\approx 22.5$ V, $V_{GS}$ = 10 V, $I_{D}$ = 50 A	_	122	_	nC
gate-drain)		$V_{DD} \approx 22.5 \text{ V}, \text{ V}_{GS}$ = 4.5 V, I <sub>D</sub> = 50 A	_	59	_	
Gate-source charge 1	Q <sub>gs1</sub>	$V_{DD}\approx 22.5 \text{ V}, \text{ V}_{GS} \text{ = } 10 \text{ V}, \text{ I}_{D} \text{ = } 50 \text{ A}$		30	_	
Gate-drain charge	Q <sub>gd</sub>		_	22	_	
Gate switch charge	Q <sub>SW</sub>			34		
Output charge	Q <sub>oss</sub>	V <sub>DS</sub> = 22.5 V, V <sub>GS</sub> = 0 V	_	98	_	

#### 6.4. Source-Drain Characteristics ( $T_a = 25 \ ^{\circ}C$ unless otherwise specified)

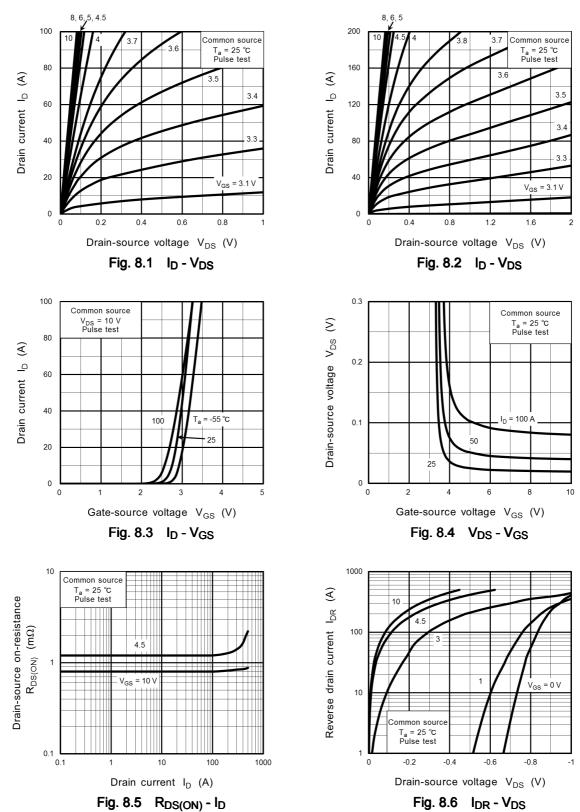
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (No	te 6) I <sub>DRP</sub>	(t = 100 μs)	_	_	500	А
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 150 A, V <sub>GS</sub> = 0 V	_	_	-1.2	V
Reverse recovery time	t <sub>rr</sub>	$V_{R}$ = 22.5 V, I <sub>DR</sub> = 37.5 A, V <sub>GS</sub>	_	58	—	ns
Reverse recovery charge	Q <sub>rr</sub>	= 0 V, -dI/dt = 100 A/μs		66	_	nC

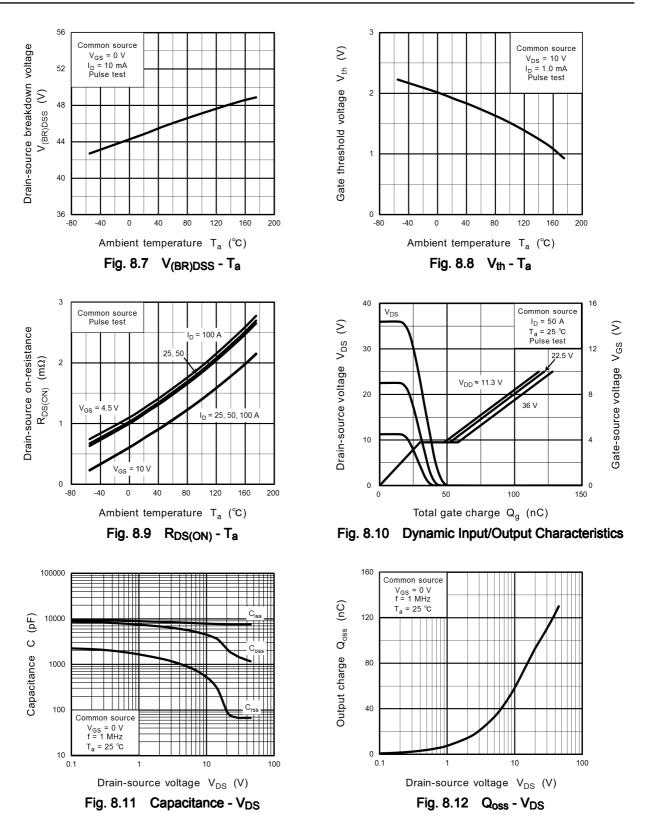
Note 6: Ensure that the channel temperature does not exceed 175 °C.

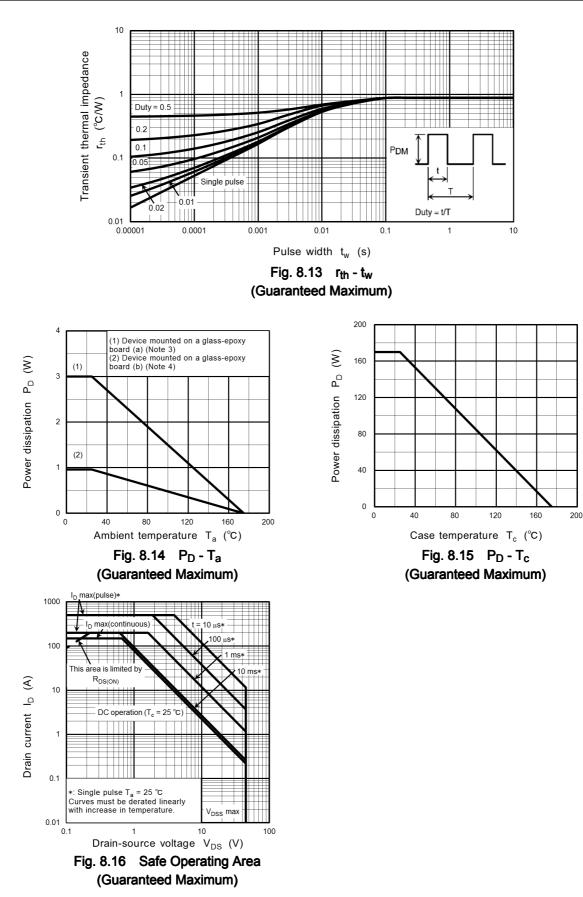
### 7. Marking



### 8. Characteristics Curves (Note)





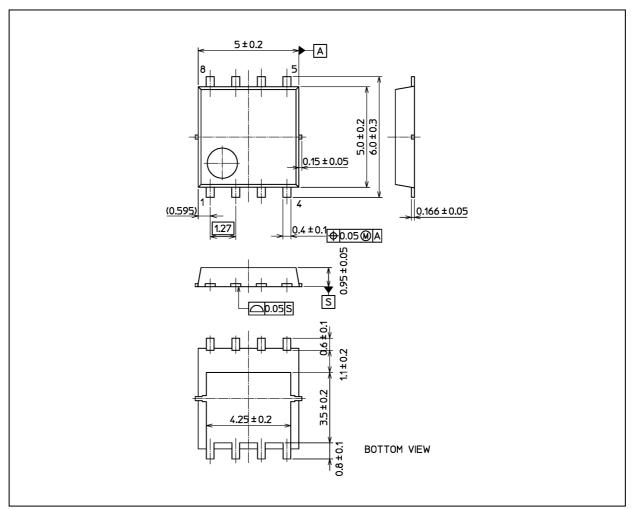


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

### TPH1R005PL

### Package Dimensions

Unit: mm



The package can be selected according to your preference. For details, please contact your TOSHIBA sales representative.

Weight: 0.087 g (typ.)

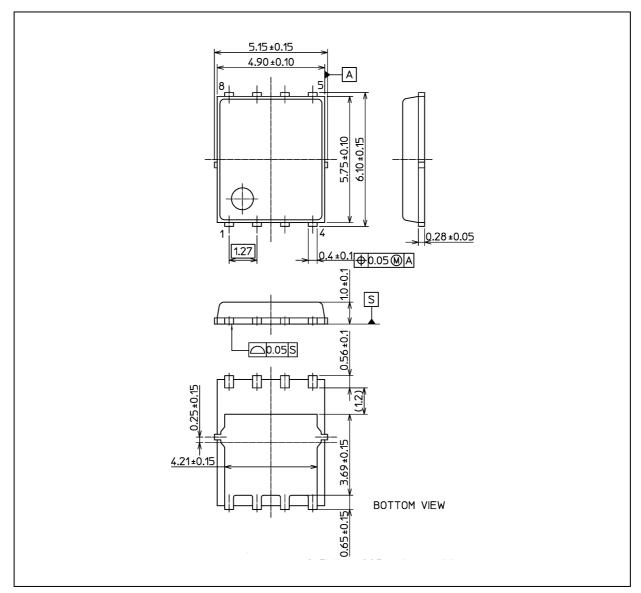
	Package Name(s)
TOSHIBA: 2-5Q1S	
Nickname: SOP Advance	



### TPH1R005PL

#### **Package Dimensions**

Unit: mm



The package can be selected according to your preference. For details, please contact your TOSHIBA sales representative.

Weight: 0.111 g (typ.)

Package Name(s)			
TOSHIBA: 2-5W1A			
Nickname: SOP Advance(N)			

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